

<u>NEWS 1</u>	Web Page URLs for STN Seminar Schedule - N. America	
<u>NEWS 2</u>	"Ask CAS" for self-help around the clock	
<u>NEWS 3</u>	JUL 12	BEILSTEIN enhanced with new display and select options, resulting in a closer connection to BABS
<u>NEWS 4</u>	AUG 02	IFIPAT/IFIUDB/IFICDB reloaded with new search and display fields
<u>NEWS 5</u>	AUG 02	CAplus and CA patent records enhanced with European and Japan Patent Office Classifications
<u>NEWS 6</u>	AUG 02	The Analysis Edition of STN Express with Discover! (Version 7.01 for Windows) now available
<u>NEWS 7</u>	AUG 27	BIOCOMMERCE: Changes and enhancements to content coverage
<u>NEWS 8</u>	AUG 27	BIOTECHABS/BIOTECHDS: Two new display fields added for legal status data from INPADOC
<u>NEWS 9</u>	SEP 01	INPADOC: New family current-awareness alert (SDI) available
<u>NEWS 10</u>	SEP 01	New pricing for the Save Answers for SciFinder Wizard within STN Express with Discover!
<u>NEWS 11</u>	SEP 01	New display format, HITSTR, available in WPIDS/WPINDEX/WPIX
<u>NEWS 12</u>	SEP 27	STANDARDS will no longer be available on STN
<u>NEWS 13</u>	SEP 27	SWETSCAN will no longer be available on STN
<u>NEWS 14</u>	OCT 28	KOREPAT now available on STN
<u>NEWS EXPRESS</u>	OCTOBER 29 CURRENT WINDOWS VERSION IS V7.01A, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 11 AUGUST 2004	
<u>NEWS HOURS</u>	STN Operating Hours Plus Help Desk Availability	
<u>NEWS INTER</u>	General Internet Information	
<u>NEWS LOGIN</u>	Welcome Banner and News Items	
<u>NEWS PHONE</u>	Direct Dial and Telecommunication Network Access to STN	
<u>NEWS WWW</u>	CAS World Wide Web Site (general information)	

Enter NEWS followed by the item number or name to see news on that specific topic.

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FILE 'HOME' ENTERED AT 15:24:35 ON 16 NOV 2004

COST IN U.S. DOLLARS		SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST		0.21	0.21

FILE 'INSPEC' ENTERED AT 15:24:47 ON 16 NOV 2004
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FILE LAST UPDATED: 15 NOV 2004 <20041115/UP>
FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
THE BASIC INDEX >>>

=> s intrinsic gallium nitride
60140 INTRINSIC
169893 GALLIUM
29974 NITRIDE
L1 1 INTRINSIC GALLIUM NITRIDE
(INTRINSIC(W)GALLIUM(W)NITRIDE)

=> i ii

L IS NOT A RECOGNIZED COMMAND

The previous command name entered was not recognized by the system.
For a list of commands available to you in the current file, enter
"HELP COMMANDS" at an arrow prompt (=>).

=> d ii 1

L1 ANSWER 1 OF 1 INSPEC (C) 2004 IEE on STN

FULL **SEARCH**
TEST **ISSN/REFS**

AN 1996:5330139 INSPEC DN B9609-2810D-002
TI High field flashover strength of **intrinsic gallium nitride** and
aluminum nitride in vacuum.
AU Khan, M.A.; Chen, O. (APA Opt. Inc., Blaine, MN, USA); Sudarshan, T.S.;
Gradinaru, G.
SO Applied Physics Letters (8 July 1996) vol.69, no.2, p.254-6. 17 refs.
Doc. No.: S0003-6951(96)03128-2
Published by: AIP
Price: CCCC 0003-6951/96/69(2)/254/3/\$10.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19960708)69:2L.254:HFFS;1-G
DT Journal
TC Experimental
CY United States
LA English

=> s semi-insulating gallium nitride

69288 SEMI
53254 INSULATING
169893 GALLIUM
29974 NITRIDE

L2 0 SEMI-INSULATING GALLIUM NITRIDE
(SEMI (W) INSULATING (W) GALLIUM (W) NITRIDE)

=> s semi insulating gallium nitride

69288 SEMI
53254 INSULATING
169893 GALLIUM
29974 NITRIDE

L3 0 SEMI INSULATING GALLIUM NITRIDE
(SEMI (W) INSULATING (W) GALLIUM (W) NITRIDE)

=> s semiinsulating gallium nitride

1616 SEMIINSULATING
169893 GALLIUM
29974 NITRIDE

L4 0 SEMIINSULATING GALLIUM NITRIDE
(SEMIINSULATING (W) GALLIUM (W) NITRIDE)

=> log y

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

FULL ESTIMATED COST

ENTRY

SESSION

5.79 6.00

STN INTERNATIONAL LOGOFF AT 15:26:24 ON 16 NOV 2004

<u>NEWS 1</u>	Web Page URLs for STN Seminar Schedule - N. America	
<u>NEWS 2</u>	"Ask CAS" for self-help around the clock	
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<u>NEWS WWW</u>	CAS World Wide Web Site (general information)	

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FILE 'HOME' ENTERED AT 17:18:09 ON 16 NOV 2004

=> file inspection
COST IN U. S. DOLLARS

SINCE FILE TOTAL
ENTRY SESSION

FULL ESTIMATED COST 0.21 0.21

FILE 'INSPEC' ENTERED AT 17:18:19 ON 16 NOV 2004

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FILE LAST UPDATED: 15 NOV 2004 <20041115/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
THE BASIC INDEX >>>

=> s insulating gan

53254 INSULATING

16401 GAN

L1 63 INSULATING GAN

(INSULATING (W) GAN)

=> s transition metals

381004 TRANSITION

109725 METALS

L2 9497 TRANSITION METALS

(TRANSITION (W) METALS)

=> s I1 and I2

L3 0 L1 AND L2

=> d I1 1-60

L1 ANSWER 1 OF 63 INSPEC (C) 2004 IEE on STN

PDF [REMOVED]
Text [REMOVED]

AN 2004:8130479 INSPEC DN A2004-22-7360L-032; B2004-11-2520D-051

TI Carrier and defect dynamics in photoexcited semi-insulating epitaxial GaN
layers.

AU Gaubas, E. ; Jursenas, S. ; Miasojedovas, S. ; Vaitkus, J. ; Zukauskas, A.
(Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)

SO Journal of Applied Physics (15 Oct. 2004) vol. 96, no. 8, p. 4326-33. 22
refs.

Doc. No. : S0021-8979(04)08919-4

Published by: AIP

Price: CCCC 0021-8979/2004/96(8) /4326(8) /\$22.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(20041015)96:8L. 4326:ODDP;1-Z

DT Journal

TC Theoretical; Experimental

CY United States

LA English

L1 ANSWER 2 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2004:8002079 INSPEC DN A2004-15-7360L-003; B2004-08-2550R-001
TI Radiation-defect-dependent photoconductivity transients and photoluminescence in semi-insulating GaN.
AU Gaubas, E. ; Kazlauskas, K. ; Tomasiunas, R. ; Vaitkus, J. ; Zukauskas, A. (Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)
SO Applied Physics Letters (21 June 2004) vol. 84, no. 25, p. 5258-60. 12 refs.
Doc. No. : S0003-6951(04)03425-4
Published by: AIP
Price: CCCC 0003-6951/2004/84(25)/5258(3) /\$20. 00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20040621)84:25L. 5258:RDDP;1-Y
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 3 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2004:7950820 INSPEC DN A2004-12-7360L-001; B2004-06-2550B-012
TI Influence of high-temperature annealing on the properties of Fe doped semi-insulating GaN structures.
AU Polyakov, A. Y. ; Smirnov, N. B. ; Govorkov, A. V. ; Shlensky, A. A. (Inst. of Rare Metals, Tolmachevsky, Russia) ; Pearton, S. J.
SO Journal of Applied Physics (15 May 2004) vol. 95, no. 10, p. 5591-6. 38 refs.
Doc. No. : S0021-8979(04)02510-1
Published by: AIP
Price: CCCC 0021-8979/2004/95(10)/5591(6) /\$22. 00
CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979(20040515)95:10L. 5591:IHTA;1-K
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 4 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2004:7926263 INSPEC DN B2004-05-2560S-035
TI Enhancement of the electrical properties of AlGaN/GaN HFETs by using undoped semi-insulating GaN.
AU Jeong, Y. H. ; Oh, C. S. ; Shin, E. H. ; Kim, J. Y. ; Yang, J. W. ; Lim, K. Y. (Dept. of Semicond. Sci. & Technol., Chonbuk Nat. Univ., Chonju, South Korea)
SO Journal of the Korean Physical Society (Jan. 2004) vol. 44, no. 1, p. 140-3.
12 refs.
Published by: Korean Phys. Soc
CODEN: KPSJAS ISSN: 0374-4884
SICI: 0374-4884(200401)44:1L. 140:EEPA;1-R
Conference: 10th Korean Conference on Semiconductors. Seoul, South Korea,

27-28 Feb 2003

DT Conference Article; Journal
TC Practical; Experimental
CY Korea, Democratic People's Republic of
LA English

L1 ANSWER 5 OF 63 INSPEC (C) 2004 IEE on STN

Full Text

AN 2004:7909801 INSPEC DN A2004-09-8115H-015; B2004-05-0520F-004
TI Growth of semi-insulating GaN layer by controlling size of nucleation sites for SAW device applications.
AU Jae-Hoon Lee; Myoung-Bok Lee; Sung-Ho Hahn; Yong-Hyun Lee; Jung-Hee Lee (Sch. of Electron. Eng. & Comput. Sci., Kyungpook Nat. Univ., Daegu, South Korea); Young-Ho Bae; Hyun Kyung Cho
S0 MRS Internet Journal of Nitride Semiconductor Research (2003) vol. 8S1. 17 refs.
Collection URL: <http://nsr.mij.mrs.org/>
Published by: Mater. Res. Soc
CODEN: MIJNF7 ISSN: 1092-5783
DT Journal
TC Practical; Experimental
CY United States
LA English

L1 ANSWER 6 OF 63 INSPEC (C) 2004 IEE on STN

Full Text

AN 2004:7903841 INSPEC DN A2004-09-6320P-001
TI Ro-vibrational modes of H2 in 4H-SiC and 2H-GaN.
AU Eberlein, T. A. G.; Huggett, L.; Jones, R. (Sch. of Phys., Exeter Univ., UK); Briddon, P. R.
S0 Physica B (31 Dec. 2003) vol. 340-342, p. 171-4. 9 refs.
Published by: Elsevier
Price: CCCC 0921-4526/2003/\$30.00
CODEN: PHYBE3 ISSN: 0921-4526
SICI: 0921-4526(20031231)340/342L:171:VM;1-B
Conference: 22nd International Conference on Defects in Semiconductors - ICDS-22. Aarhus, Denmark, 28 July-1 Aug 2003
DT Conference Article; Journal
TC Theoretical
CY Netherlands
LA English

L1 ANSWER 7 OF 63 INSPEC (C) 2004 IEE on STN

Full Text

AN 2004:7855798 INSPEC DN A2004-06-7360L-001; B2004-03-2520D-047
TI Properties of Fe-doped semi-insulating GaN structures.
AU Polyakov, A. Y.; Smirnov, N. B.; Govorkov, A. V. (Inst. of Rare Metals, Tolmachevsky, Russia); Pearton, S. J.

S0 Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (Jan. 2004) vol. 22, no. 1, p. 120-5. 37 refs.
Doc. No. : S0734-211X(04)03601-7
Published by: AIP for American Vacuum Soc
Price: CCCC 1071-1023/2004/22(1)/120/6/\$19. 00
CODEN: JVTBD9 ISSN: 1071-1023
SICI: 1071-1023(200401)22:1L. 120:PDSI;1-4
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 8 OF 63 INSPEC (C) 2004 IEE on STN

 
Full Text References

AN 2004:7821192 INSPEC DN A2004-03-6630J-005
TI Hydrogen molecules in 4H-SiC and 2H-GaN.
AU Eberlein, T. A. G. ; Huggett, L. ; Jones, R. (Sch. of Phys., Exeter Univ., UK) ; Briddon, P. R.
S0 Journal of Physics: Condensed Matter (8 Oct. 2003) vol. 15, no. 39, p. S2897-902. 11 refs.
Doc. No. : S0953-8984(03)67271-1
Published by: IOP Publishing
Price: CCCC 0953-8984/03/392897+06\$30. 00
CODEN: JC0MEL ISSN: 0953-8984
SICI: 0953-8984(20031008)15:39L. s2897:HM;1-A
Conference: Workshop on 'Physics of Group IV Materials'. Exeter, UK, 7-10 April 2003
DT Conference Article; Journal
TC Theoretical
CY United Kingdom
LA English

L1 ANSWER 9 OF 63 INSPEC (C) 2004 IEE on STN

 
Full Text References

AN 2003:7770510 INSPEC DN A2003-24-7360L-001; B2003-12-2520D-019
TI Electrical and optical properties of Fe-doped semi-insulating GaN templates.
AU Polyakov, A. Y. ; Smirnov, N. B. ; Govorkov, A. V. (Inst. of Rare Metals, Moscow, Russia) ; Pearton, S. J.
S0 Applied Physics Letters (20 Oct. 2003) vol. 83, no. 16, p. 3314-16. 20 refs.
Doc. No. : S0003-6951(03)05042-3
Published by: AIP
Price: CCCC 01/03/6951/2003/83(16)/3314(3) /\$20. 00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20031020)83:16L. 3314:EOPD;1-1
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 10 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7756693 INSPEC DN A2003-23-8115H-005; B2003-11-0520F-075
TI Role of potential barriers in epitaxial layers of semi-insulating GaN
layers.
AU Vaitkus, J.V. ; Gaubas, E. (Inst. of Mater. Sci. & Appl. Res., Vilnius
Univ., Lithuania) ; Sakai, S. ; Lacroix, Y. ; Tao Wang ; Smith, K.M. ; Rahman,
M. ; Cunningham, W.
SO Diffusion and Defect Data Part B (Solid State Phenomena) (2003) vol. 93,
p. 301-6. 12 refs.
Published by: Balaban Publishers; Scitec Publications
CODEN: DDBPE8 ISSN: 1012-0394
SICI: 1012-0394(2003)93L:301:RPBE;1-Y
DT Journal
TC Experimental
CY Switzerland
LA English

L1 ANSWER 11 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7741695 INSPEC DN A2003-21-7220P-002
TI Thermoelectric effect spectroscopy measurements on semi-insulating GaN.
AU Pavlovic, M. ; Desnica, U.V. (Ruder Boskovic Inst., Zagreb, Croatia) ; Fang,
Z.-Q. ; Look, D.C.
SO Vacuum (9 May 2003) vol. 71, no. 1-2, p. 153-8. 28 refs.
Published by: Elsevier
Price: CCCC 0042-207X/03/\$30.00
CODEN: VACUAV ISSN: 0042-207X
SICI: 0042-207X(20030509)71:1/2L:153:TESM;1-R
Conference: 9th Joint Vacuum Conference (JVC-9). Schloss Seggau, Austria,
16-20 June 2002
DT Conference Article; Journal
TC Experimental
CY United Kingdom
LA English

L1 ANSWER 12 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7728893 INSPEC DN A2003-20-7320D-040; B2003-10-2520D-045
TI Two-dimensional electron gases induced by polarization charges in AlN/GaN
heterostructure grown by plasma-assisted molecular-beam epitaxy.
AU Jeganathan, K. ; Ide, T. ; Shimizu, M. ; Okumura, H. (Power Electron. Res.
Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki, Japan)
SO Journal of Applied Physics (1 Sept. 2003) vol. 94, no. 5, p. 3260-3. 18 refs.
Doc. No. : S0021-8979(03)07218-9
Published by: AIP
Price: CCCC 0021-8979/2003/94(5)/3260(4)/\$20.00

CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979 (20030901) 94:5L. 3260:DEGI;1-R
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 13 OF 63 INSPEC (C) 2004 IEE on STN

Full Text 

AN 2003:7723750 INSPEC DN A2003-20-7860H-005; B2003-10-4220-016
TI Luminescence properties of charged dislocations in semi-insulating **GaN**:Zn.
AU Srinivasan, S. ; Cai, J. ; Contreras, O. ; Ponce, F. A. (Dept. of Phys. & Astron., Arizona State Univ., Tempe, AZ, USA) ; Look, D. C. ; Molnar, R. J.
SO Physica Status Solidi C (2002) no. 1, p. 508-11. 7 refs.
Published by: Wiley-VCH
Price: CCCC 1610-1634/02/00012-0508\$17.50+.50/0
CODEN: PSSCGL ISSN: 1610-1634
SICI: 1610-1634(2002)1L. 508:LPCD;1-G
Conference: International Workshop on Nitride Semiconductors (IWN 2002). Aachen, Germany, 22-25 July 2002

DT Conference Article; Journal
TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 14 OF 63 INSPEC (C) 2004 IEE on STN

Full Text 

AN 2003:7653110 INSPEC DN A2003-14-7240-011; B2003-07-4210-017
TI Deep-defect-induced quenching effects in semi-insulating **GaN** layers detected by photoelectrical spectroscopic techniques.
AU Witte, H. ; Krtschil, A. ; Lisker, M. ; Schrenk, E. ; Christen, J. ; Krost, A. (Inst. of Exp. Phys., Otto-von-Guericke-Univ., Magdeburg, Germany) ; Kuhn, B. ; Scholz, F.
SO Applied Physics Letters (9 June 2003) vol. 82, no. 23, p. 4083-5. 16 refs.
Published by: AIP
Price: CCCC 01/03/6951/2003/82(23)/4083(3) /\$20.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20030609)82:23L. 4083:DDIQ;1-V

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 15 OF 63 INSPEC (C) 2004 IEE on STN

Full Text 

AN 2003:7650116 INSPEC DN B2003-07-0520F-069
TI Engineering of an insulating buffer and use of AlN interlayers: two optimisations for AlGaN-GaN HEMT-like structures.

AU Bougrioua, Z. (CRHEA, CNRS, Valbonne, France); Moerman, I. ; Nistor, L. ; Van Daele, B. ; Monroy, E. ; Palacios, T. ; Calle, F. ; Leroux, M.
SO Physica Status Solidi C (2003) no. 3, p. 93-100. 12 refs.
Published by: Wiley-VCH
Price: CCCC 0031-8965/03/19501-0093\$17.50+.50/0
ISSN: 1610-1634
SICI: 1610-1634(2003)3L. 93:EIBI;1-0
DT Journal
TC Practical; Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 16 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7583016 INSPEC DN A2003-10-7125T-005; B2003-05-2520D-046
TI The franz-keldysh effect in shocked GaN:Mg.
AU Peng, H.Y. ; McCluskey, M.D. ; Gupta, Y.M. (Dept. of Phys., Washington State Univ., Pullman, WA, USA) ; Kneissl, M. ; Johnson, N.M.
SO Applied Physics Letters (31 March 2003) vol. 82, no. 13, p. 2085-7. 23 refs.
Published by: AIP
Price: CCCC 01/03/6951/2003/82(13)/2085(3) /\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20030331)82:13L. 2085:FKES;1-1
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 17 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7562747 INSPEC DN A2003-09-6855-004; B2003-04-2520D-063
TI Growth of Fe doped semi-insulating GaN by metalorganic chemical vapor deposition.
AU Heikman, S. ; Keller, S. ; DenBaars, S.P. ; Mishra, U.K. (Dept. of Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)
SO Applied Physics Letters (15 July 2002) vol. 81, no. 3, p. 439-41. 28 refs.
Doc. No. : S0003-6951(02)01826-0
Published by: AIP
Price: CCCC 01/03/6951/2002/81(3)/439(3) /\$19.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20020715)81:3L. 439:GDSI;1-T
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 18 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7555977 INSPEC DN A2003-08-7855-037
TI Annealing effect on the Al+ implantation induced deep traps in GaN film.
AU Xu Xiao-liang; He Hai-yan; Liu Hong-tu; Shi Chao-shu (Struct. Res. Lab., Univ. of Sci. & Technol. of China, Hefei, China); Ge Wei-kun; Luo, E. Z. ; Sundaravel, B. ; Wilson, I. H.
SO Chinese Journal of Liquid Crystals and Displays (Aug. 2002) vol.17, no. 4, p. 243-52. 22 refs.
Published by: Science Press
ISSN: 1007-2780
SICI: 1007-2780(200208)17:4L. 243:AEII;1-8
DT Journal
TC Experimental
CY China
LA Chinese

L1 ANSWER 19 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7501464 INSPEC DN A2003-04-6855-046; B2003-02-2560S-018
TI Comparison of high mobility AlGaN/GaN heterostructures grown by MBE on HVPE GaN templates and directly nucleated on sapphire.
AU Manfra, M. J. ; Weimann, N. G. ; Hsu, J. W. P. ; Pfeiffer, L. N. ; West, K. W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Molnar, R. J.
SO 2002 International Conference on Molecular Beam Epitaxy (Cat. No. 02EX607) Piscataway, NJ, USA: IEEE, 2002. p. 231-2 of 424 pp.
Conference: San Francisco, CA, USA, 15-20 Sept 2002
Sponsor(s): IEEE Lasers & Electro-Opt. Soc
Price: CCCC 0-7803-7581-5/02/\$17. 00
ISBN: 0-7803-7581-5
DT Conference Article
TC Experimental
CY United States
LA English

L1 ANSWER 20 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2003:7490791 INSPEC DN A2003-03-7240-006; B2003-02-4210-007
TI Photo-stimulated current spectroscopy and its application in detecting aluminum implantation-induced deep traps in GaN.
AU Xiaoliang Xu; Haiyan He; Hongtu Liu; Chaoshu Shi (Struct. Res. Lab., Acad. Sinica, Hefei, China); Weikun Ge; Luo, E. Z. ; Sundaravel, B. ; Wilson, I. H.
SO Thin Solid Films (2 Sept. 2002) vol. 416, no. 1-2, p. 294-301. 31 refs.
Doc. No.: S0040-6090(02)00681-8
Published by: Elsevier
Price: CCCC 0040-6090/02/\$22. 00
CODEN: THSFAP ISSN: 0040-6090
SICI: 0040-6090(20020902)416:1/2L. 294:PSCS;1-Y
DT Journal
TC Experimental
CY Switzerland

LA English

L1 ANSWER 21 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2002:7453703 INSPEC DN B2002-12-2560S-026
TI Characterization of GaN based MESFETs by comparing electroluminescence, photoionization and cathodoluminescence spectroscopy.
AU Armani, N. (Ist. MASPEC, CNR, Parma, Italy); Chini, A. ; Manfredi, M. ; Meneghesso, G. ; Pavesi, M. ; Grillo, V. ; Salviati, G. ; Zanoni, E.
SO Microscopy of Semiconducting Materials 2001. Proceedings of the Royal Microscopical Society Conference
Editor(s): Cullis, A.G. ; Hutchinson, J.L.
Bristol, UK: IOP Publishing, 2001. p.503-6 of xiv+610 pp. 11 refs.
Conference: Oxford, UK, 25-29 March 2001
ISBN: 0-7503-0818-4
DT Conference Article
TC Practical; Experimental
CY United Kingdom
LA English

L1 ANSWER 22 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2002:7399617 INSPEC DN A2002-22-7155-003; B2002-11-2520D-019
TI Thermoelectric effect spectroscopy of deep levels in semi-insulating GaN.
AU Desnica, U. V. ; Pavlovic, M. (Boskovic (R.) Inst., Zagreb, Croatia); Fang, Z.-Q. ; Look, D.C.
SO Journal of Applied Physics (1 Oct. 2002) vol. 92, no. 7, p. 4126-8. 28 refs.
Doc. No. : S0021-8979(02)08919-3
Published by: AIP
Price: CCCC 0021-8979/2002/92(7)/4126(3) /\$19. 00
CODEN: JAPIAU ISSN: 0021-8979
SICI: 0021-8979(20021001)92:7L:4126:TESD;1-H
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 23 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2002:7383461 INSPEC DN A2002-21-7340L-005; B2002-10-2530B-027
TI High mobility AlGaN/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy.
AU Manfra, M. J. ; Weimann, N. G. ; Hsu, J. W. P. ; Pfeiffer, L. N. ; West, K. W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Syed, S. ; Stormer, H. L. ; Pan, W. ; Lang, D. V. ; Chu, S. N. G. ; Kowach, G. ; Sergent, A. M. ; Caissie, J. ; Molvar, K. M. ; Mahoney, L. J. ; Molnar, R. J.
SO Journal of Applied Physics (1 July 2002) vol. 92, no. 1, p. 338-45. 15 refs.

Doc. No. : S0021-8979 (02)03414-X

Published by: AIP

Price: CCCC 0021-8979/2002/92(1)/338(8) /\$19. 00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979 (20020701) 92:1L. 338:HMAH;1-#

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 24 OF 63 INSPEC (C) 2004 IEE on STN

AN 2002:7380070 INSPEC DN A2002-21-7865K-006; B2002-10-2520D-049

TI Optical metastability in undoped GaN grown on Ga-rich GaN buffer layers.

AU Dhar, S. ; Ghosh, S. (Sch. of Phys. Sci., Jawaharlal Nehru Univ., New Delhi, India)

SO Applied Physics Letters (17 June 2002) vol. 80, no. 24, p. 4519-21. 24 refs.

Doc. No. : S0003-6951 (02)06221-6

Published by: AIP

Price: CCCC 0003-6951/2002/80(24)/4519(3) /\$19. 00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951 (20020617) 80:24L. 4519:0MUG;1-1

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 25 OF 63 INSPEC (C) 2004 IEE on STN

AN 2002:7367591 INSPEC DN A2002-20-8115G-008; B2002-10-2530B-006

TI Dislocation and morphology control during molecular-beam epitaxy of AlGaN/GaN heterostructures directly on sapphire substrates.

AU Manfra, M. J. ; Weimann, N. G. ; Hsu, J. W. P. ; Pfeiffer, L. N. ; West, K. W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA) ; Chu, S. N. G.

SO Applied Physics Letters (19 Aug. 2002) vol. 81, no. 8, p. 1456-8. 9 refs.

Doc. No. : S0003-6951 (02)04731-9

Published by: AIP

Price: CCCC 0003-6951/2002/81(8)/1456(3) /\$19. 00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951 (20020819) 81:8L. 1456:DMCD;1-2

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 26 OF 63 INSPEC (C) 2004 IEE on STN

AN 2002:7348972 INSPEC DN A2002-18-7865K-045

TI Optical study of GaN doped with Mn grown by metal organic vapor phase epitaxy.
AU Korotkov, R.Y.; Gregie, J.M.; Wessels, B.W. (Dept. of Mater. Sci. & Eng., Northwestern Univ., Evanston, IL, USA)
SO GaN and Related Alloys - 2000. Symposium (Materials Research Society Symposium Proceedings Vol. 639)
Editor(s): Wetzel, C.; Shur, M.S.; Mishra, U.K.; Gil, B.; Kishino, K.
Warrendale, PA, USA: Mater. Res. Soc, 2001. p. G3.7.1-6 of xxvii+938 pp. 19 refs.
Conference: Boston, MA, USA, 27 Nov-1 Dec 2000
DT Conference Article
TC Experimental
CY United States
LA English

L1 ANSWER 27 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2002:7166632 INSPEC DN A2002-05-7340L-014; B2002-03-2560S-010
TI Back bias effects in AlGaN/GaN HFETs.
AU Uren, M.J.; Herbert, D.; Martin, T.; Hughes, B.T.; Birbeck, J.; Balmer, R.; Piddock, A.J. (QinetiQ Ltd., Malvern, UK); Jones, S.K.
SO Physica Status Solidi A (16 Nov. 2001) vol. 188, no. 1, p. 195-8. 10 refs.
Published by: Wiley-VCH
Price: CCCC 0031-8965/01/18811-0195\$17.50+.50/0
CODEN: PSSABA ISSN: 0031-8965
SICI: 0031-8965(20011116)188:1L.195:BBEA;1-7
Conference: Fourth International Conference on Nitride Semiconductors.
Denver, CO, USA, 16-20 July 2001
DT Conference Article; Journal
TC Practical; Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 28 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 2002:7159990 INSPEC DN A2002-05-8115G-012; B2002-02-0520D-053
TI Growth and characterisation of high electron mobility transistors on 4H-SiC by ammonia molecular beam epitaxy.
AU Webb, J.; Haipeng Tang; Bardwell, J.A.; Rolfe, S.; Ying Liu; Lapointe, A.; Marshall, P. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada); MacElwee, T.W.
SO Physica Status Solidi A (16 Nov. 2001) vol. 188, no. 1, p. 271-4. 9 refs.
Published by: Wiley-VCH
Price: CCCC 0031-8965/01/18811-0271\$17.50+.50/0
CODEN: PSSABA ISSN: 0031-8965
SICI: 0031-8965(20011116)188:1L.271:GCHE;1-Q
Conference: Fourth International Conference on Nitride Semiconductors.
Denver, CO, USA, 16-20 July 2001
DT Conference Article; Journal

TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 29 OF 63 INSPEC (C) 2004 IEE on STN

 Full Text

AN 2002:7143723 INSPEC DN A2002-04-7320D-011; B2002-02-2530B-020
TI 2DEG characteristics of AlN/GaN heterointerface on sapphire substrates
grown by plasma-assisted MBE.
AU Jeganathan, K. ; Ide, T. ; Shen, S. X. Q. ; Shimizu, M. ; Okumura, H. (Power
Electron. Res. Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki,
Japan)
SO Physica Status Solidi B (1 Nov. 2001) vol. 228, no. 2, p. 613-16. 17 refs.
Published by: Wiley-VCH
Price: CCCC 0370-1972/01/22811-0613\$17.50+.50/0
CODEN: PSSBBD ISSN: 0370-1972
SICI: 0370-1972(20011101)228:2L. 613:2CHS;1-U
Conference: Fourth International Conference on Nitride Semiconductors.
Denver, CO, USA, 16-20 July 2001
DT Conference Article; Journal
TC Experimental
CY Germany, Federal Republic of
LA English

L1 ANSWER 30 OF 63 INSPEC (C) 2004 IEE on STN

 Full Text

AN 2002:7137121 INSPEC DN B2002-02-2560S-013
TI Fabrication and characterization of GaN junction field effect transistors.
AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA) ; Lester, L. F. ; Baca,
A. G. ; Shul, R. J. ; Chang, P. C. ; Willison, C. G. ; Mishra, U. K. ; Denbaars,
S. P. ; Zolper, J. C.
SO GaN and Related Alloys - 1999. Symposium (Materials Research Society
Symposium Proceedings Vol. 595)
Editor(s): Myers, T. H. ; Feenstra, R. M. ; Shur, M. S. ; Amano, H.
Warrendale, PA, USA: Mater. Res. Soc, 2000. p. W4.9.1-7 of xxvii+10002 pp.
21 refs.
Conference: Boston, MA, USA, 28 Nov-3 Dec 1999
ISBN: 1-55899-503-X
DT Conference Article
TC Experimental; Practical
CY United States
LA English

L1 ANSWER 31 OF 63 INSPEC (C) 2004 IEE on STN

 Full Text

AN 2001:7011094 INSPEC DN A2001-18-6855-086; B2001-09-0520F-088
TI A single step nucleation process for growth of GaN-based materials by
OMVPE.

AU Smart, J. A. (Dept. of Electr. Eng., Cornell Univ., Ithaca, NY, USA); Shealy, J. R.
SO WOCS DICE 2000. 24th Workshop on Compound Semiconductor Devices and Integrated Circuits
Ann Arbor, MI, USA: Univ. Michigan, 2000. p. I-5, I-6 of xxii+196 pp. 1 refs.
Conference: Aegean Sea, Greece, 29 May-2 June 2000
ISBN: 0-9703111-0-9
DT Conference Article
TC Practical; Experimental
CY United States
LA English

L1 ANSWER 32 OF 63 INSPEC (C) 2004 IEE on STN

 
Full Text

AN 2001:6991427 INSPEC DN A2001-17-8115G-035; B2001-09-0520D-045
TI Advances in III-nitride growth by ammonia-MBE.
AU Webb, J. B.; Tang, H.; Bardwell, J. A. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada)
SO Proceedings of International Workshop on Nitride Semiconductors
Tokyo, Japan: Inst. Pure & Appl. Phys, 2000. p. 228-32 of 1002 pp. 9 refs.
Conference: Nagoya, Japan, 24-27 Sept 2000
Sponsor(s): Japan Soc. Appl. Phys.; Japan Soc. Promotion of Sci
ISBN: 4-900526-13-4
DT Conference Article
TC General Review; Experimental; Practical
CY Japan
LA English

L1 ANSWER 33 OF 63 INSPEC (C) 2004 IEE on STN

 
Full Text

AN 2001:6932166 INSPEC DN B2001-07-2560S-001
TI Effect of growth termination conditions on the performance of AlGaN/GaN high electron mobility transistors.
AU Keller, S.; Vetary, R.; Parish, G.; DenBaars, S. P.; Mishra, U. K. (Dept. Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)
SO Applied Physics Letters (14 May 2001) vol. 78, no. 20, p. 3088-90. 14 refs.
Doc. No.: S0003-6951(01)05420-1
Published by: AIP
Price: CCCC 0003-6951/2001/78(20)/3088(3)/\$18.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(20010514)78:20L.3088:EGTC;1-L
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 34 OF 63 INSPEC (C) 2004 IEE on STN

Full
Text

INSPEC
REFERENCES

AN 2000:6795326 INSPEC DN B2001-02-1350F-014
TI Recessed-gate GaN MESFET using ICP-RIE for high temperature microwave
applications.
AU Lee, C. ; Lu, W. (Dept. of Electr. & Comput. Eng., Illinois Univ., Urbana,
IL, USA); Piner, E. ; Adesida, I.
SO 58th DRC. Device Research Conference. Conference Digest (Cat. No. 00TH8526)
Piscataway, NJ, USA: IEEE, 2000. p. 41-2 of xii+176 pp. 6 refs.
Conference: Denver, CO, USA, 19-21 June 2000
Sponsor(s): IEEE Electron Devices Soc
ISBN: 0-7803-6472-4
DT Conference Article
TC Application; Practical; Experimental
CY United States
LA English

L1 ANSWER 35 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

Full
Text

INSPEC
REFERENCES

AN 2000:6766620 INSPEC DN A2001-01-7830-012
TI Infrared studies on GaN single crystals and homoepitaxial layers.
AU Frayssinet, E. ; Knap, W. (Groupe d'Etudes des Semicond., CNRS,
Montpellier, France); Prystawko, P. ; Leszczynski, M. ; Grzegory, I. ; Suski,
T. ; Beaumont, B. ; Gibart, P.
SO Journal of Crystal Growth (Sept. 2000) vol. 218, no. 2-4, p. 161-6. 24 refs.
Doc. No. : S0022-0248(00)00537-6
Published by: Elsevier
Price: CCCC 0022-0248/2000/\$20.00
CODEN: JCRGAE ISSN: 0022-0248
SICI: 0022-0248(200009)218:2/4L.161:ISSC;1-0
DT Journal
TC Experimental
CY Netherlands
LA English

L1 ANSWER 36 OF 63 INSPEC (C) 2004 IEE on STN

Full
Text

INSPEC
REFERENCES

AN 2000:6572341 INSPEC DN A2000-11-6855-060; B2000-06-0520J-004
TI Near defect free GaN substrates.
AU Porowski, S. (High Pressure Res. Center, Acad. of Sci., Warsaw, Poland)
SO GaN and Related Alloys. Symposium
Editor(s): Pearton, S. J. ; Kuo, C. ; Wright, A. F. ; Uenoyama, T.
Warrendale, PA, USA: Mater. Res. Soc, 1999. p. G1.3/11 pp. of 1028 pp. 37
refs.
Conference: Boston, MA, USA, 30 Nov-4 Dec 1998
ISBN: 1-55899-443-2
DT Conference Article
TC Experimental
CY United States

LA English

L1 ANSWER 37 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Search

AN 2000:6540346 INSPEC DN B2000-05-1350F-005
TI Epitaxially-grown GaN junction field effect transistors.
AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA); Lester, L. F. ; Baca, A. G. ; Shul, R. J. ; Chang, P. C. ; Willison, C. G. ; Mishra, U.K. ; Denbaars, S. P. ; Zolper, J. C.
S0 IEEE Transactions on Electron Devices (March 2000) vol. 47, no. 3, p. 507-11.
25 refs.
Doc. No. : S0018-9383(00)01938-9
Published by: IEEE
Price: CCCC 0018-9383/2000/\$10. 00
CODEN: IETDAI ISSN: 0018-9383
SICI: 0018-9383(200003)47:3L. 507:EGJF;1-4
DT Journal
TC Application; Practical; Experimental
CY United States
LA English

L1 ANSWER 38 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Search

AN 1999:6410037 INSPEC DN A2000-01-8115J-001; B2000-01-0520X-001
TI Insulating GaN:Zn layers grown by hydride vapor phase epitaxy on SiC substrates.
AU Kuznetsov, N. I. ; Nikolaev, A. E. ; Zubrilov, A. S. (A. F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Melnik, Yu. V. ; Dmitriev, V. A.
S0 Applied Physics Letters (15 Nov. 1999) vol. 75, no. 20, p. 3138-40. 25 refs.
Doc. No. : S0003-6951(99)03446-4
Published by: AIP
Price: CCCC 0003-6951/99/75(20)/3138(3)/\$15. 00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19991115)75:20L. 3138:ILGH;1-T
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 39 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Search

AN 1999:6402056 INSPEC DN A1999-24-8115H-014; B1999-12-0520F-095
TI Properties of GaN homoepitaxial layers grown on GaN epitaxial wafers.
AU Dmitriev, V. ; Nikolaev, A. (A. F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Cherenkov, A. ; Tsvetkov, D. ; Stepanov, S. ; Kuznetsov, N. ; Nikitina, I. ; Kovarsky, A. ; Yagovkina, M. ; Davidov, V.
S0 Wide-Bandgap Semiconductors for High Power, High Frequency and High

Temperature. Symposium

Editor(s): DenBaars, S. ; Palmour, J. ; Shur, M. ; Spencer, M.

Warrendale, PA, USA: Mater. Res. Soc, 1998. p. 451-6 of xiii+565 pp. 14 refs.

Conference: San Francisco, CA, USA, 13-15 April 1998

ISBN: 1-55899-418-1

DT Conference Article

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 40 OF 63 INSPEC (C) 2004 IEE on STN

Full Text REFERENCES

AN 1999:6386564 INSPEC DN A1999-23-0762-006; B1999-12-72300-007

TI The effect of threading dislocations, Mg doping, and etching on the spectral responsivity in GaN-based ultraviolet detectors.

AU Torvik, J.T. ; Pankove, J. I. (Astralux Inc., Boulder, CO, USA) ; Nakamura, S. ; Grzegory, I. ; Porowski, S.

SO Journal of Applied Physics (15 Oct. 1999) vol. 86, no. 8, p. 4588-93. 32 refs.

Doc. No. : S0021-8979(99)09820-5

Published by: AIP

Price: CCCC 0021-8979/99/86(8)/4588(6) /\$15.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(19991015)86:8L. 4588:ETDD;1-7

DT Journal

TC Application; Experimental

CY United States

LA English

L1 ANSWER 41 OF 63 INSPEC (C) 2004 IEE on STN

Full Text REFERENCES

AN 1999:6325956 INSPEC DN A1999-19-8115G-001; B1999-10-0520D-001

TI Semi-insulating C-doped GaN and high-mobility AlGaN/GaN heterostructures grown by ammonia molecular beam epitaxy.

AU Webb, J.B. ; Tang, H. ; Rolfe, S. ; Bardwell, J.A. (Inst. for Microstruct. Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada)

SO Applied Physics Letters (16 Aug. 1999) vol. 75, no. 7, p. 953-5. 17 refs.

Doc. No. : S0003-6951(99)00933-X

Published by: AIP

Price: CCCC 0003-6951/99/75(7)/953(3) /\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19990816)75:7L. 953:SIDH;1-5

DT Journal

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 42 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 1999:6276753 INSPEC DN A1999-15-7865K-002
TI Optical properties of a high-quality insulating GaN epilayer.
AU Zeng, K.C. ; Lin, J.Y. ; Jiang, H.X. (Dept. of Phys., Kansas State Univ., Manhattan, KS, USA) ; Wei Yang
SO Applied Physics Letters (21 June 1999) vol. 74, no. 25, p. 3821-3. 14 refs.
Doc. No. : S0003-6951(99)04025-5
Published by: AIP
Price: CCCC 0003-6951/99/74(25)/3821(3) /\$15. 00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19990621)74:25L. 3821:OPHQ;1-G
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 43 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 1999:6254375 INSPEC DN A1999-13-6150C-001; B1999-07-0510-001
TI Near defect free GaN substrates.
AU Porowski, S. (High Pressure Res. Center, Polish Acad. of Sci., Warsaw, Poland)
SO MRS Internet Journal of Nitride Semiconductor Research (1999) vol. 4S1. 37 refs.
Collection URL: <http://nsr.mii.mrs.org/>
Published by: Mater. Res. Soc
CODEN: MIJNF7 ISSN: 1092-5783
DT Journal
TC General Review; Experimental
CY United States
LA English

L1 ANSWER 44 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 1999:6156537 INSPEC DN A1999-06-7865K-008; B1999-03-2530C-038
TI Dynamics of fundamental optical transitions in group III-nitrides.
AU Jiang, H.X. ; Lin, J.Y. (Dept. of Phys., Kansas State Univ., Manhattan, KS, USA)
SO Proceedings of the SPIE - The International Society for Optical Engineering (1998) vol. 3277, p. 108-18. 19 refs.
Published by: SPIE-Int. Soc. Opt. Eng
Price: CCCC 0277-786X/98/\$10. 00
CODEN: PSISDG ISSN: 0277-786X
SICI: 0277-786X(1998)3277L. 108:DFOT;1-Y
Conference: Ultrafast Phenomena in Semiconductors II. San Jose, CA, USA, 28-29 Jan 1998
Sponsor(s): SPIE
DT Conference Article; Journal

TC Experimental
CY United States
LA English

L1 ANSWER 45 OF 63 INSPEC (C) 2004 IEE on STN

 
Text 

AN 1998:6015588 INSPEC DN A9820-7320-027; B9810-2520D-014
TI Magnetic resonance of dopants and defects in GaN-based materials and devices.
AU Carlos, W. E. (Naval Res. Lab., Washington, DC, USA)
SO 7th International Conference on Shallow-Level Centers in Semiconductors
Editor(s): Ammerlaan, C. A. J. ; Pajot, B.
Singapore: World Scientific, 1997. p.13-23 of xviii+534 pp. 37 refs.
Conference: Amsterdam, Netherlands, 17-19 July 1996
Sponsor(s): Found. Phys. ; Found. Fundamental Res. Matter; Philips Res. ;
Int. Sci. Found. ; Univ. Amsterdam
ISBN: 981-02-2928-3
DT Conference Article
TC Experimental
CY Singapore
LA English

L1 ANSWER 46 OF 63 INSPEC (C) 2004 IEE on STN

 
Text 

AN 1998:5907712 INSPEC DN A9812-7360F-001; B9806-2520D-027
TI Deep centers in n-GaN grown by reactive molecular beam epitaxy.
AU Fang, Z.-Q. ; Look, D. C. (Res. Center, Wright State Univ., Dayton, OH, USA) ; Kim, W. ; Fan, Z. ; Botchkarev, A. ; Morkoc, H.
SO Applied Physics Letters (4 May 1998) vol. 72, no. 18, p. 2277-9. 10 refs.
Doc. No.: S0003-6951(98)02818-6
Published by: AIP
Price: CCCC 0003-6951/98/72(18)/2277(3) /\$15. 00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19980504)72:18L. 2277:DCGR;1-G
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 47 OF 63 INSPEC (C) 2004 IEE on STN

 
Text 

AN 1998:5808269 INSPEC DN A9804-7855-045
TI Photoluminescence of Fe-complexes in GaN.
AU Thurian, P. ; Hoffmann, A. ; Eckey, L. ; Maxim, P. ; Heitz, R. ; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany) ; Pressel, K. ; Meyer, B.-K. ; Schneider, J. ; Bauer, J. ; Kunzer, M.
SO III-V Nitrides. Symposium
Editor(s): Ponce, F. A. ; Moustakas, T. D. ; Akasaki, I. ; Monemar, B. A.

Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p. 707-12 of xxv+1251 pp. 11 refs.

Conference: Boston, MA, USA, 2-6 Dec 1996

DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 48 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 1998:5800812 INSPEC DN A9804-6170B-002

TI Investigation of vacancies in GaN by positron annihilation.

AU Jorgensen, L. V. ; Kruseman, A. C. ; Schut, H. ; Van Veen, A. (Interfaculty Reactor Inst., Delft Univ. of Technol., Netherlands) ; Fanciulli, M. ; Moustakas, T. D.

SO III-V Nitrides. Symposium

Editor(s) : Ponce, F. A. ; Moustakas, T. D. ; Akasaki, I. ; Monemar, B. A.

Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p. 853-8 of xxv+1251 pp. 24 refs.

Conference: Boston, MA, USA, 2-6 Dec 1996

DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 49 OF 63 INSPEC (C) 2004 IEE on STN

Full Text References

AN 1997:5780136 INSPEC DN A9802-7360F-015; B9801-2520D-079

TI Fe-related defects in GaN epilayers.

AU Thurian, P. ; Heitz, R. ; Eckey, L. ; Maxim, P. ; Kutzer, V. ; Hoffmann, A. ; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany) ; Pressel, K. ; Meyer, B.-K.

SO 23rd International Conference on the Physics of Semiconductors

Editor(s) : Scheffler, M. ; Zimmermann, R.

Singapore: World Scientific, 1996. p. 2897-900 vol. 4 of 4 vol.

(xxxviii+xxvii+xxx+xxvi+3460) pp. 6 refs.

Conference: Berlin, Germany, 21-26 July 1996

ISBN: 981-02-2777-9

DT Conference Article

TC Experimental

CY Singapore

LA English

L1 ANSWER 50 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

Full Text References

AN 1997:5676103 INSPEC DN A9719-7865-063; B9710-0510D-089

TI Electrical and optical properties of semi-insulating GaN.

AU Look, D. C. ; Reynolds, D. C. (Res. Center, Wright State Univ., Dayton, OH,

USA); Jones, R.L.; Kim, W.; Aktas, Oe.; Botchkarev, A.; Salvador, A.; Morkoc, H.

S0 Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (Feb. 1997) vol. 44, no. 1-3, p. 423-6. 20 refs.

Published by: Elsevier

Price: CCCC 0921-5107/97/\$17.00

CODEN: MSBTEK ISSN: 0921-5107

SICI: 0921-5107(199702)44:1/3L.423:E0PS;1-V

Conference: 3rd International Workshop on Expert Evaluation and Control of Compound Semiconductor Materials and Technologies. Freiburg, Germany, 12-15 May 1996

Sponsor(s): Deutsche Forschungsgemeinschaft; Fraunhofer IAF; Freiberger Compound Mater.; et al

DT Conference Article; Journal

TC Experimental

CY Switzerland

LA English

L1 ANSWER 51 OF 63 INSPEC (C) 2004 IEE on STN

Full Text

AN 1997:5598632 INSPEC DN B9707-1350F-018

TI Bias dependent microwave performance of AlGaN/GaN MODFET's up to 100 V.

AU Wu, Y.-F.; Keller, S.; Kozodoy, P.; Keller, B.P.; Parikh, P.; Kapolnek, D.; Denbaars, S.P.; Mishra, U.K. (Dept. of Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)

S0 IEEE Electron Device Letters (June 1997) vol. 18, no. 6, p. 290-2. 8 refs.

Published by: IEEE

Price: CCCC 0741-3106/97/\$10.00

CODEN: EDLEDZ ISSN: 0741-3106

SICI: 0741-3106(199706)18:6L.290:BDMP;1-X

DT Journal

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 52 OF 63 INSPEC (C) 2004 IEE on STN

Full Text

AN 1997:5581086 INSPEC DN A9712-6170T-008; B9706-2550B-035

TI Ion implantation doping of OMCDV grown GaN.

AU Edwards, A.; Rao, M.V. (Dept. of Electr. & Comput. Eng., George Mason Univ., Fairfax, VA, USA); Molnar, B.; Wickenden, A.E.; Holland, O.W.; Chi, P.H.

S0 Journal of Electronic Materials (March 1997) vol. 26, no. 3, p. 334-9. 34 refs.

Published by: TMS

CODEN: JECMA5 ISSN: 0361-5235

SICI: 0361-5235(199703)26:3L.334:ID0G;1-C

Conference: Proceedings of the 38th Electronic Materials Conference. Santa Barbara, CA, USA, 26-28 June 1996

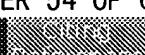
DT Conference Article; Journal
TC Experimental
CY United States
LA English

L1 ANSWER 53 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

Full Text 

AN 1997:5555400 INSPEC DN A9710-7360F-009; B9705-2520D-087
TI Characterization of GaN using thermally stimulated current and photocurrent spectroscopies and its application to UV detectors.
AU Huang, Z. C. (Hughes STX Corp., Greenbelt, MD, USA); Chen, J. C.; Wickenden, D.
S0 Journal of Crystal Growth (Jan. 1997) vol. 170, no. 1-4, p. 362-6. 12 refs.
Doc. No.: S0022-0248(96)00576-3
Published by: Elsevier
Price: CCCC 0022-0248/97/\$17.00
CODEN: JCRGAE ISSN: 0022-0248
SICI: 0022-0248(199701)170:1/4L.362:CTS;1-9
Conference: 8th International Conference on Metalorganic Vapour Phase Epitaxy. Cardiff, UK, 9-13 June 1996
DT Conference Article; Journal
TC Experimental
CY Netherlands
LA English

L1 ANSWER 54 OF 63 INSPEC (C) 2004 IEE on STN

Full Text 

AN 1997:5550853 INSPEC DN A9710-7855-018; B9705-2520D-074
TI Excited states of Fe³⁺ in GaN.
AU Heitz, R.; Maxim, P.; Eckey, L.; Thurian, P.; Hoffmann, A.; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany); Pressel, K.; Meyer, B. K.
S0 Physical Review B (Condensed Matter) (15 Feb. 1997) vol. 55, no. 7, p. 4382-7. 43 refs.
Doc. No.: S0163-1829(97)00807-2
Published by: APS through AIP
Price: CCCC 0163-1829/97/55(7)/4382(6) /\$10.00
CODEN: PRBMDO ISSN: 0163-1829
SICI: 0163-1829(19970215)55:7L.4382:ES;1-M

DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 55 OF 63 INSPEC (C) 2004 IEE on STN

Full Text 

AN 1996:5472856 INSPEC DN A9704-7155-012
TI Deep states in GaN studied by thermally stimulated current spectroscopy.

AU Huang, Z. C. (Hughes STX Corp., Greenbelt, MD, USA); Chen, J. C.; Mott, D. B.
SO Gallium Nitride and Related Materials. First International Symposium
Editor(s): Ponce, F. A.; Dupuis, R. D.; Nakamura, S.; Edmond, J. A.
Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p. 703-8 of xxi+970 pp. 13
refs.
Conference: Boston, MA, USA, 27 Nov-1 Dec 1995
DT Conference Article
TC Experimental
CY United States
LA English

L1 ANSWER 56 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Reference

AN 1996:5311100 INSPEC DN A9616-7155-003; B9608-2520D-136
TI Thermally stimulated current trap in GaN.
AU Look, D.C.; Fang, Z.-Q. (Res. Center, Wright State Univ., Dayton, OH,
USA); Kim, W.; Aktas, O.; Botchkarev, A.; Salvador, A.; Morkoc, H.
SO Applied Physics Letters (24 June 1996) vol. 68, no. 26, p. 3775-7. 15 refs.
Doc. No.: S0003-6951(96)02826-4
Published by: AIP
Price: CCCC 0003-6951/96/68(26)/3775/3/\$10.00
CODEN: APPLAB ISSN: 0003-6951
SICI: 0003-6951(19960624)68:26L.3775:TSCT;1-T
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 57 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Reference

AN 1996:5238653 INSPEC DN A9610-0762-010; B9605-7230C-032
TI Photoconducting ultraviolet detectors based on GaN films grown by electron
cyclotron resonance molecular beam epitaxy.
AU Misra, M. (Radiation Monitoring Devices Inc., Watertown, MA, USA);
Moustakas, T. D.; Vaudo, R. P.; Singh, R.; Shah, K. S.
SO Proceedings of the SPIE - The International Society for Optical
Engineering (1995) vol. 2519, p. 78-86. 10 refs.
Published by: SPIE-Int. Soc. Opt. Eng
Price: CCCC 0 8194 1878 1/95/\$6.00
CODEN: PSISDG ISSN: 0277-786X
SICI: 0277-786X(1995)2519L.78:PUDB;1-Z
Conference: X-Ray and Ultraviolet Sensors and Applications. San Diego, CA,
USA, 13-14 July 1995
Sponsor(s): SPIE
DT Conference Article; Journal
TC Experimental
CY United States
LA English

L1 ANSWER 58 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Abstract References

AN 1992:4145231 INSPEC DN A9212-8115G-001; B9206-0510D-116
TI Atomic layer epitaxy of GaN over sapphire using switched metalorganic
chemical vapor deposition.
AU Khan, M.A. ; Skogman, R.A. ; Van Hove, J.M. ; Olson, D.T. ; Kuznia, J.N. (APA
Opt. Inc., Blaine, MN, USA)
SO Applied Physics Letters (16 March 1992) vol. 60, no. 11, p. 1366-8. 9 refs.
Price: CCCC 0003-6951/92/111366-03\$03. 00
CODEN: APPLAB ISSN: 0003-6951
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 59 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Abstract References

AN 1982:1802623 INSPEC DN A82013422; B82009757
TI Dielectric properties of reactively sputtered gallium nitride-films.
AU Lakshmi, E. (Dept. of Phys., Indian Inst. of Technol., Delhi, New Delhi,
India)
SO Thin Solid Films (4 Sept. 1981) vol. 83, no. 1, p. L137-9. 3 refs.
CODEN: THSFAP ISSN: 0040-6090
DT Journal
TC Experimental
CY Switzerland
LA English

L1 ANSWER 60 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Abstract References

AN 1976:932411 INSPEC DN A76062370; B76028430
TI Optimized growth conditions and properties of n-type and **insulating GaN**.
AU Jacob, G. ; Madar, R. ; Hallais, J. (Lab. d'Electronique et de Phys. Appl.,
Limeil-Brevannes, France)
SO Materials Research Bulletin (April 1976) vol. 11, no. 4, p. 445-50. 9 refs.
CODEN: MRBUAC ISSN: 0025-5408
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 61 OF 63 INSPEC (C) 2004 IEE on STN

Full Text Abstract References

AN 1975:817993 INSPEC DN B75037918
TI Electroluminescent semiconductor display.
AU Pankove, J. I.
CS RCA

PI USA 3864592 4 Feb. 1975
AD 22 March 1973
DT Patent
TC Practical
CY United States
LA English

L1 ANSWER 62 OF 63 INSPEC (C) 2004 IEE on STN

FULL **REFS**
Text **CONTINUATION**

AN 1974:688105 INSPEC DN A74073235
TI Photoemission from GaN.
AU Pankove, J. I. ; Schade, H. (RCA Labs., Princeton, NJ, USA)
SO Applied Physics Letters (1 July 1974) vol. 25, no. 1, p. 53-5. 8 refs.
CODEN: APPLAB ISSN: 0003-6951
DT Journal
TC Experimental
CY United States
LA English

L1 ANSWER 63 OF 63 INSPEC (C) 2004 IEE on STN

FULL **REFS**
Text **CONTINUATION**

AN 1974:582796 INSPEC DN A74001414
TI Luminescence of insulating Be-doped and Li-doped GaN.
AU Pankove, J. I. ; Duffy, M. T. ; Miller, E. A. ; Berkeyheiser, J. E. (RCA Labs.,
Princeton, NJ, USA)
SO Journal of Luminescence (Sept. 1973) vol. 8, no. 1, p. 89-93. 12 refs.
CODEN: JLUMA8 ISSN: 0022-2313
DT Journal
TC Experimental
CY Netherlands
LA English

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